

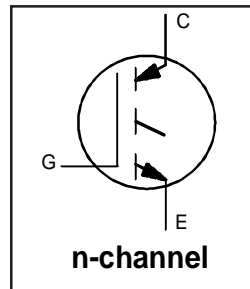
IRG4BC30FPbF

INSULATED GATE BIPOLAR TRANSISTOR

Fast Speed IGBT

Features

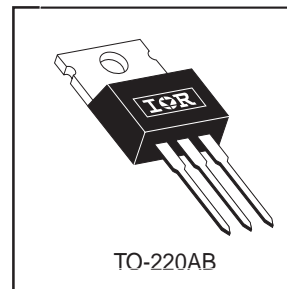
- Fast: optimized for medium operating frequencies (1-5 kHz in hard switching, >20 kHz in resonant mode).
- Generation 4 IGBT design provides tighter parameter distribution and higher efficiency than Generation 3
- Industry standard TO-220AB package
- Lead-Free



$V_{CES} = 600V$
$V_{CE(on)} \text{ typ.} = 1.59V$
@ $V_{GE} = 15V, I_C = 17A$

Benefits

- Generation 4 IGBTs offer highest efficiency available
- IGBTs optimized for specified application conditions
- Designed to be a "drop-in" replacement for equivalent industry-standard Generation 3 IR IGBTs



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Breakdown Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	31	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	17	
I_{CM}	Pulsed Collector Current ①	120	
I_{LM}	Clamped Inductive Load Current ②	120	
V_{GE}	Gate-to-Emitter Voltage	± 20	V
E_{ARV}	Reverse Voltage Avalanche Energy ③	10	mJ
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	100	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	42	
T_J	Operating Junction and	-55 to + 150	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	---	1.2	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.5	---	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	---	80	
Wt	Weight	2.0 (0.07)	---	g (oz)

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_C = 250\mu\text{A}$
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ④	18	—	—	V	$V_{GE} = 0V, I_C = 1.0A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.69	—	V/°C	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	—	1.59	1.8	V	$I_C = 17A$ $V_{GE} = 15V$ See Fig.2, 5
		—	1.99	—		
		—	1.7	—		
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		$I_C = 17A, T_J = 150^\circ\text{C}$ $V_{CE} = V_{GE}, I_C = 250\mu\text{A}$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/°C	$V_{CE} = V_{GE}, I_C = 250\mu\text{A}$
g_{fe}	Forward Transconductance ⑤	6.1	10	—	S	$V_{CE} = 100V, I_C = 17A$
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{GE} = 0V, V_{CE} = 600V$
		—	—	2.0		$V_{GE} = 0V, V_{CE} = 10V, T_J = 25^\circ\text{C}$
		—	—	1000		$V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	51	77	nC	$I_C = 17A$ $V_{CC} = 400V$ $V_{GE} = 15V$ See Fig. 8
Q_{ge}	Gate - Emitter Charge (turn-on)	—	7.9	12		
Q_{gc}	Gate - Collector Charge (turn-on)	—	19	28		
$t_{d(on)}$	Turn-On Delay Time	—	21	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 17A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 23\Omega$ Energy losses include "tail"
t_r	Rise Time	—	15	—		
$t_{d(off)}$	Turn-Off Delay Time	—	200	300		
t_f	Fall Time	—	180	270	mJ	See Fig. 10, 11, 13, 14
E_{on}	Turn-On Switching Loss	—	0.23	—		
E_{off}	Turn-Off Switching Loss	—	1.18	—		
E_{ts}	Total Switching Loss	—	1.41	2.0	ns	$T_J = 150^\circ\text{C}$, $I_C = 17A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 23\Omega$ Energy losses include "tail"
$t_{d(on)}$	Turn-On Delay Time	—	20	—		
t_r	Rise Time	—	16	—		
$t_{d(off)}$	Turn-Off Delay Time	—	290	—		
t_f	Fall Time	—	350	—	mJ	See Fig. 13, 14
E_{ts}	Total Switching Loss	—	2.5	—		
L_E	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	1100	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ $f = 1.0MHz$ See Fig. 7
C_{oes}	Output Capacitance	—	74	—		
C_{res}	Reverse Transfer Capacitance	—	14	—		

Notes:

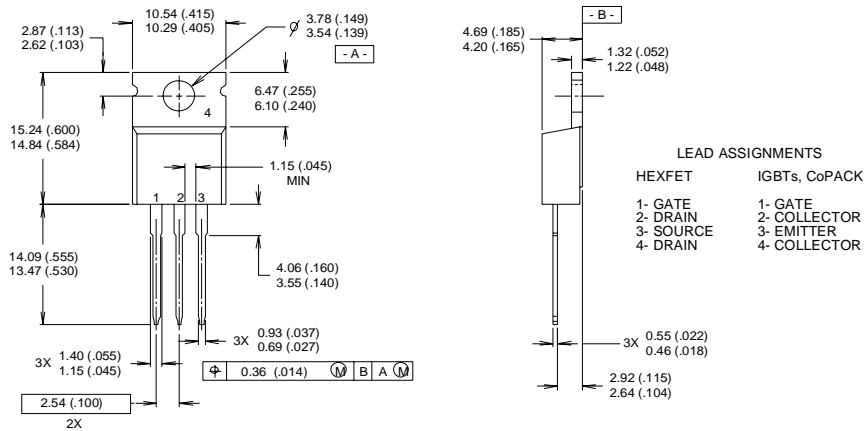
- ① Repetitive rating; $V_{GE} = 20V$, pulse width limited by max. junction temperature. (See fig. 13b)
- ② $V_{CC} = 80\%(V_{CES})$, $V_{GE} = 20V$, $L = 10\mu\text{H}$, $R_G = 23\Omega$, (See fig. 13a)
- ③ Repetitive rating; pulse width limited by maximum junction temperature.
- ④ Pulse width $\leq 80\mu\text{s}$; duty factor $\leq 0.1\%$.
- ⑤ Pulse width $5.0\mu\text{s}$, single shot.

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TO-220AB Package Outline

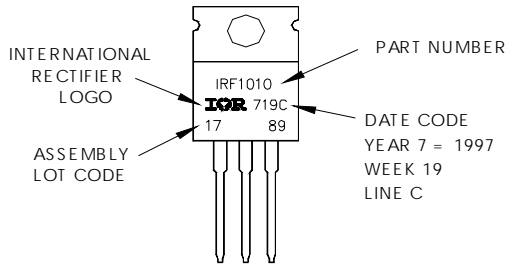
Dimensions are shown in millimeters (inches)



- NOTES:
- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
 - 2 CONTROLLING DIMENSION : INCH
 - 3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
 - 4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
 LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE "C"
Note: "P" in assembly line position indicates "Lead-Free"



Data and specifications subject to change without notice.

